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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		Atty. Docket SUND 466	Application No. 10/603,659				
		Applicant Mu-Jen LAI et al.					
		Filing Date June 26, 2003	Group 2814				
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date
	AA						
	AB						
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	AF						
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	AH						
				FOREIGN PATENT DOCUMENTS			
		Document Number	Date	Country	Class	Sub-Class	Trans-lation
	AI						
	AJ						
	AK						
	AL						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
	AM	"ZnTe-GaN heterostructure switching device", A. G. Drizhuk et al.; Tech. Phys. Lett. 23 (10), October 1997; 1997 American Institute of Physics; pages 809 and 810					
	AN	"Growth of GaN on Si substrates - roles of BP thin layer" Optical Materials, S. Nishimura et al., one page - ISI Web of Science 6.0					
Examiner <i>M. J. Lai</i>		Date Considered 8-17-04					
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							